

Ultra low losses

Passivation: Silicon Oxide

$V_{RRM} = 1200V$

$I_F = 8A$

Die Size: 2,4 x 2,4mm

Maximum rated values:

Parameter	Symbol	min	max	Unit
Repetitive peak reverse voltage	V_{RRM}	-	1200	V
Working Peak Reverse Voltage	V_{RWM}	-	1200	V
DC Blocking Voltage	V_R	-	1200	V
Continuous forward current	I_F	-	8	A
Repetitive peak forward current* (Square Wave, 20 kHz)	I_{FRM}	-	16	A
Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60 Hz)	I_{FSM}	-	tdb	A
Avalanche Energy	E_{AVL}	-	tdb	mj
Junction temperature	T_j	-	150	°C
Operating and Storage Temperature	T_{STG}, T_J		-65 to 150	°C

*- Limited by T_{vj} max

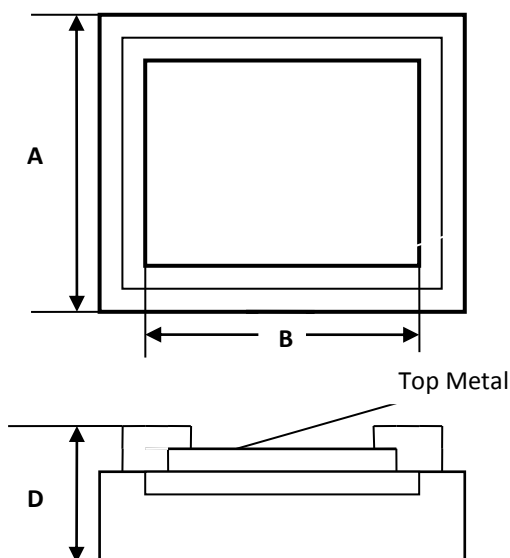
Diode Characteristics values:

Parameter	Symbol	Conditions	min	typ	max	Unit	
Continuous forward voltage	V_F	$I_F=8A, T_{vj}=25^{\circ}C$	-	2.4	3.0	V	
Continuous forward voltage	V_F	$I_F=8A, T_{vj}=150^{\circ}C$	-	2.3	2.9	V	
Continuous reverse current	I_R	$V_R=1200V$	$T_{vj}=25^{\circ}C$	-	10	50	μA
			$T_{vj}=125^{\circ}C$	-	1.0	1.5	mA
Reverse Recovery Time	t_{rr}	$I_F=1A, V_R=30V, dl_F/dt=200A/\mu S$	-	40	50	nS	

Mechanical properties:

Top metal: **Al-Ti** – for Wire Bonding

Backside metal: **Ti-Ni-Ag** – for Soldering



DIM	ITEM	μm
A_x A_y	Die Size	2400 2400
D	Thickness	350 max
Scribe Line Width		60